

**IN THE SPECIFICATION**

Please amend the specification as follows:

Page 5, in the paragraph beginning on line 12, change as follows:

a' FIG. 1B illustrates the step of partially depositing an etch stop layer 13 on an etching area of the first silica layer 12. The etch stop layer 13 is partially deposited by lift-off or etching.

**IN THE CLAIMS**

Please cancel claims 8 without prejudice and amend the claims as follows:

- a' 1. (Amended) A silica microstructure fabrication method comprising the steps of:
- a'        depositing an etch stop layer on an etching area of a portion of a first silica layer formed on a semiconductor substrate;
- forming a second silica layer on the surfaces of the etch stop layer and the first silica layer;
- forming a mask patterned according to the shape of the etching area on the surface of the second silica layer;
- removing the second silica layer from the etching area using the mask by dry etching; and
- removing the etch stop layer by wet etching.